

Advance Data

Insulated Gate Bi-Polar Transistor Type T0600TB45A

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	4500	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	2800	V
V_{GES}	Peak gate – emitter voltage	± 20	V

	RATINGS	MAXIMUM LIMITS	UNITS
$I_{C(DC)}$	DC collector current, IGBT	600	A
I_{CRM}	Repetitive peak collector current, $t_p=1ms$, IGBT	1200	A
$I_{F(DC)}$	Continuous DC forward current, Diode	600	A
I_{FRM}	Repetitive peak forward current, $t_p=1ms$, Diode	1200	A
I_{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=60\%V_{RRM}$, Diode (Note 4)	9400	A
I_{FSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, Diode (Note 4)	10300	A
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	4.8	kW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	2000	A/ μs
T_j	Operating temperature range.	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range.	-40 to +125	$^{\circ}C$

Notes: -

- 1) Unless otherwise indicated $T_j = 125^{\circ}C$.
- 2) $T_{sink} = 25^{\circ}C$, double side cooled.
- 3) Maximum commutation loop inductance 200nH.
- 4) Half-sinewave, $125^{\circ}C$ T_j initial.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS	
$V_{CE(sat)}$	Collector – emitter saturation voltage	-	2.9	3.3	$I_C = 600A, V_{GE} = 15V, T_j = 25^\circ C$	V	
		-	3.7	4.1	$I_C = 600A, V_{GE} = 15V$	V	
V_{T0}	Threshold voltage	-	-	1.8	Current range: 200 – 600A	V	
r_T	Slope resistance	-	-	3.84		$m\Omega$	
$V_{GE(TH)}$	Gate threshold voltage	-	5.3	-	$V_{CE} = V_{GE}, I_C = 60mA$	V	
I_{CES}	Collector – emitter cut-off current	-	13	30	$V_{CE} = V_{CES}, V_{GE} = 0V$	mA	
I_{GES}	Gate leakage current	-	-	± 7	$V_{GE} = \pm 20V$	μA	
C_{ies}	Input capacitance	-	100	-	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	nF	
$t_{d(on)}$	Turn-on delay time	-	1.6	-	$I_C = 600A, V_{CE} = 2800V, di/dt = 2000A/\mu s$ $V_{GE} = \pm 15V, L_s = 200nH$ $R_{g(ON)} = 6.8\Omega, R_{g(OFF)} = 11\Omega, C_{GE} = 68nF$ Integral diode used as freewheel diode (Note 3, 4 & 5)	μs	
$t_r(V)$	Rise time	-	2.7	-		μs	
$Q_{g(on)}$	Turn-on gate charge	-	8	-		μC	
E_{on}	Turn-on energy	-	4.6	-		J	
$t_{d(off)}$	Turn-off delay time	-	3.4	-		μs	
$t_f(I)$	Fall time	-	2.5	-		μs	
$Q_{g(off)}$	Turn-off gate charge	-	3	-		μC	
E_{off}	Turn-off energy	-	2.9	-		J	
I_{SC}	Short circuit current	-	1900	-		$V_{GE} = +15V, V_{CC} = 2800V, V_{CEmax} \leq V_{CES}, t_p \leq 25\mu s$	A

Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V_F	Forward voltage	-	3.6	3.9	$I_F = 600A, T_j = 25^\circ C$	V
		-	3.7	4.0	$I_F = 600A$	V
V_{T0}	Threshold voltage	-	-	2.18	Current range 200-600A	V
r_T	Slope resistance	-	-	3.03		$m\Omega$
I_{rm}	Peak reverse recovery current	-	640	-	$I_F = 600A, V_{GE} = \pm 15V, di/dt = 2000A/\mu s$	A
Q_{rr}	Recovered charge	-	700	-		μC
t_{rr}	Reverse recovery time, 50% chord	-	1.2	-		μs
E_r	Reverse recovery energy	-	0.9	-		J

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R_{thJK}	Thermal resistance junction to sink, IGBT	-	-	21.8	Double side cooled	K/kW
		-	-	36.8	Collector side cooled	K/kW
		-	-	53.5	Emitter side cooled	K/kW
R_{thJK}	Thermal resistance junction to sink, Diode	-	-	43.2	Double side cooled	K/kW
		-	-	68	Cathode side cooled	K/kW
		-	-	118	Anode side cooled	K/kW
F	Mounting force	15	20	25	Note 2	kN
W_t	Weight	-	1.2	-		kg

Notes:-

- 1) Unless otherwise indicated $T_j = 125^\circ C$.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive
- 4) E_{on} integration time 15 μs from 10% rising I_C .
- 5) E_{off} integration time 15 μs from 90% falling V_{GE} .

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

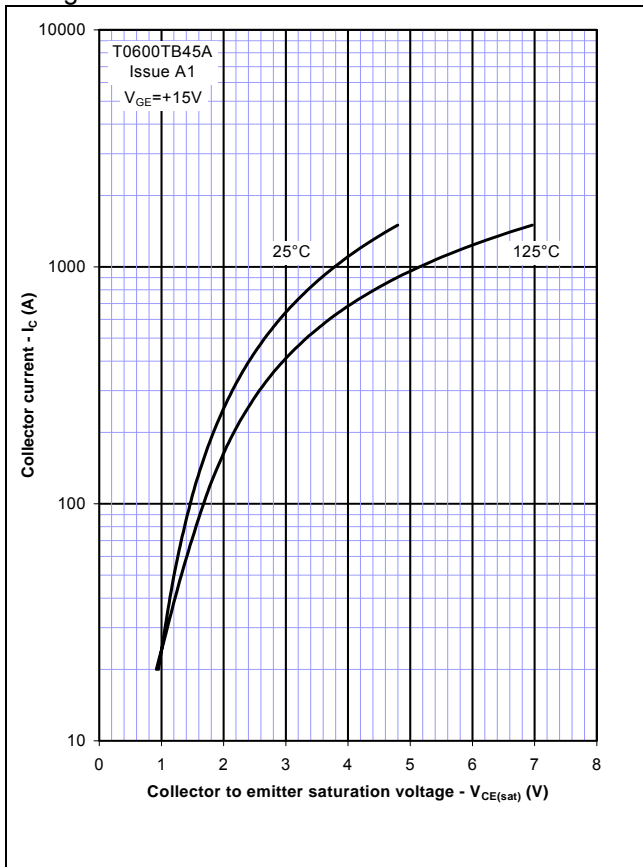


Figure 2 – Typical output characteristic

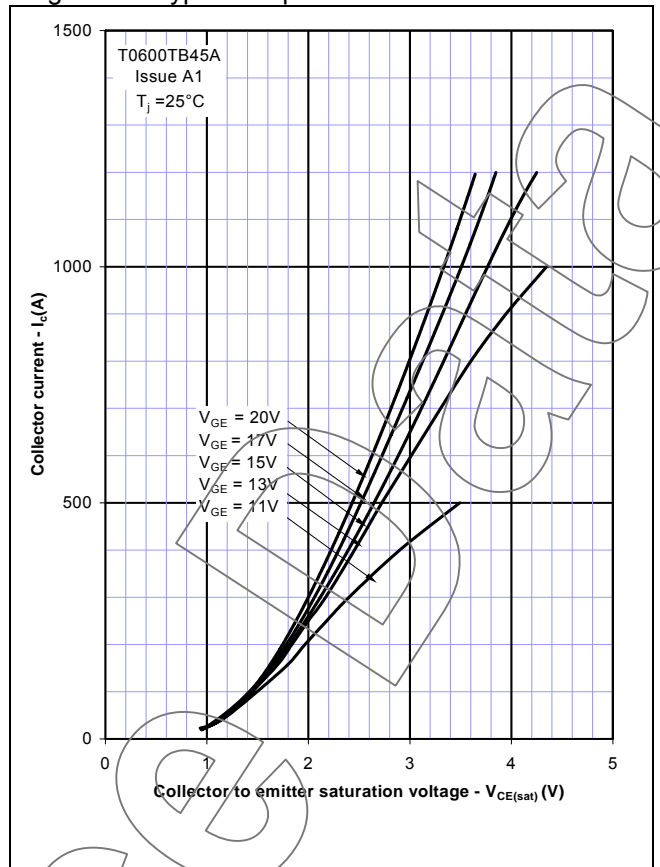


Figure 3 – Typical output characteristic

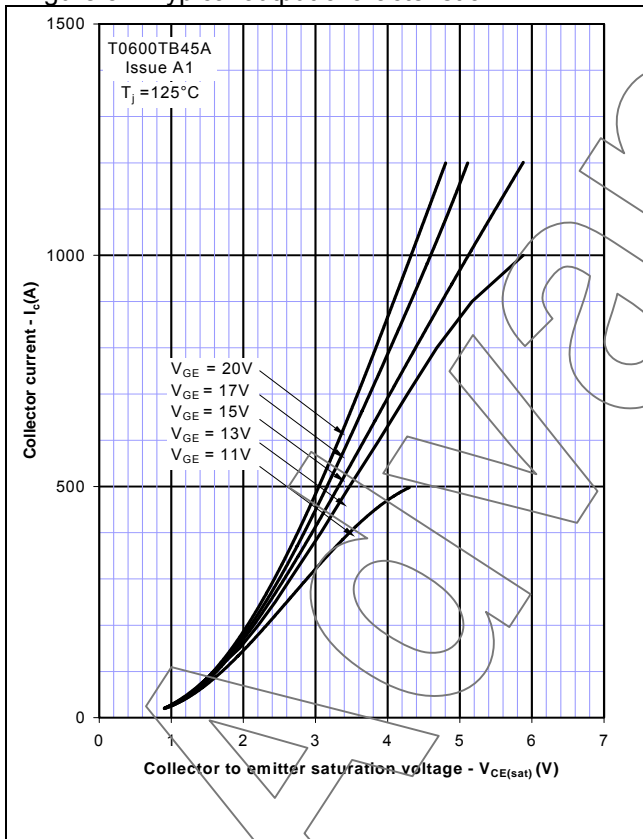


Figure 4 – Typical turn-on delay time vs gate resistance

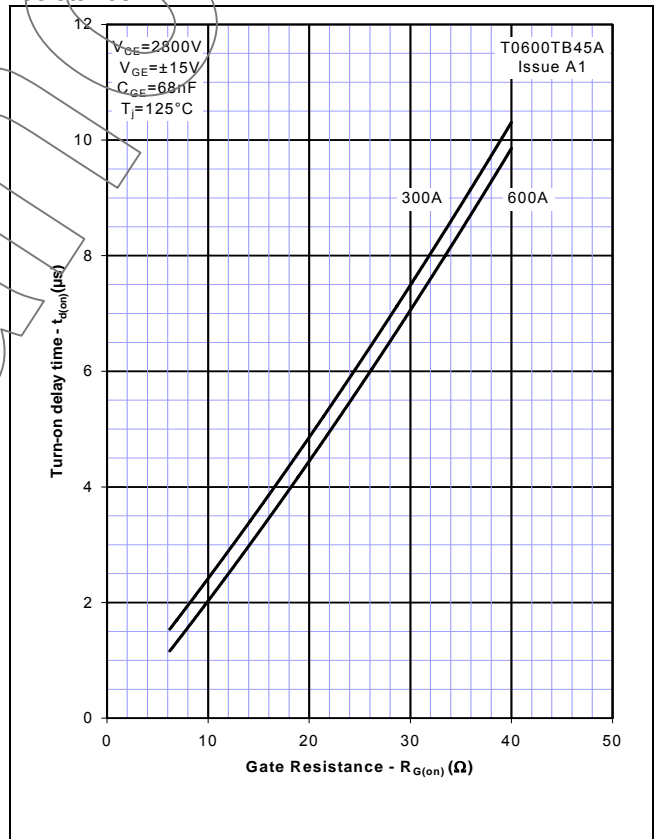


Figure 5 – Typical turn-off delay time vs. gate resistance

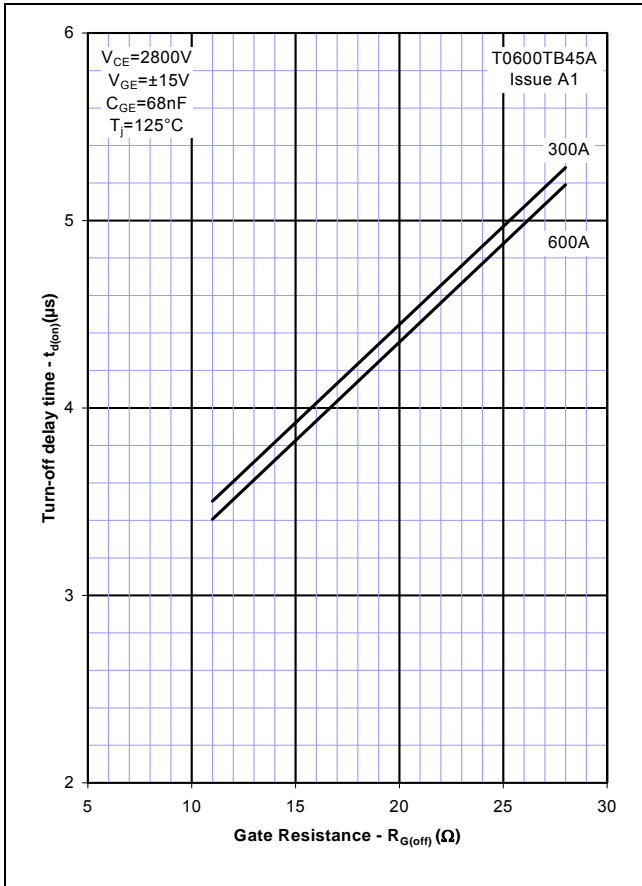


Figure 6 – Typical turn-on energy vs. collector current

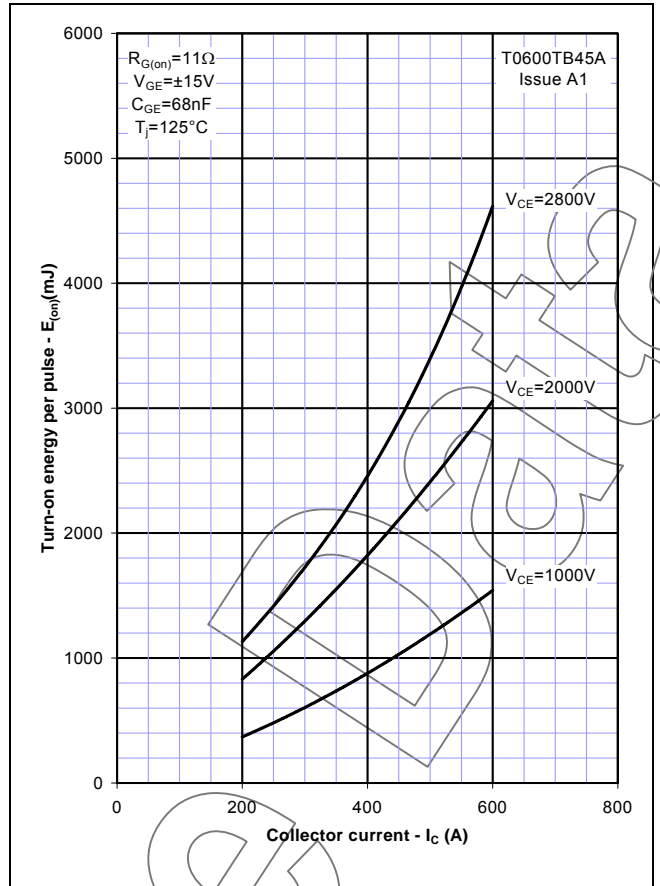


Figure 7 – Typical turn-on energy vs. di/dt

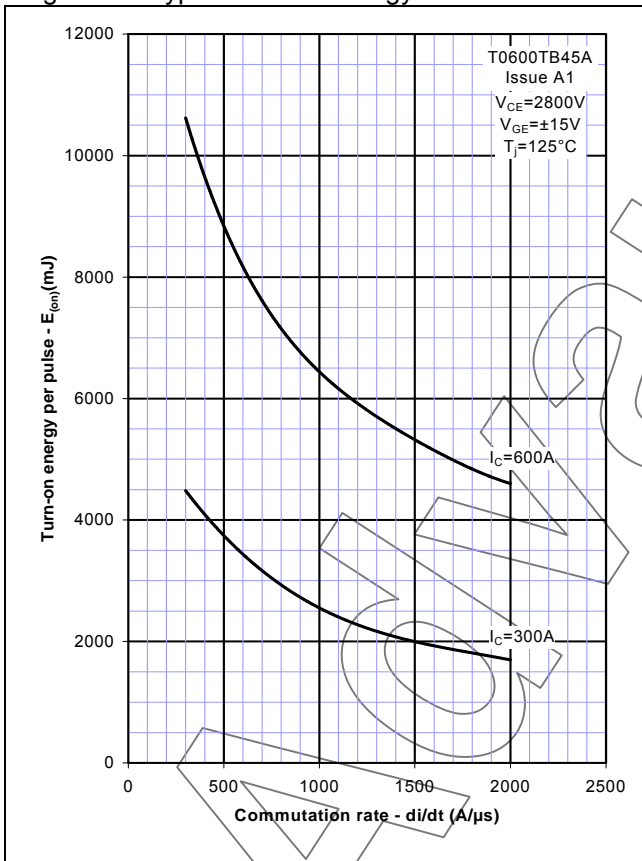


Figure 8 – Typical turn-off energy vs. collector current

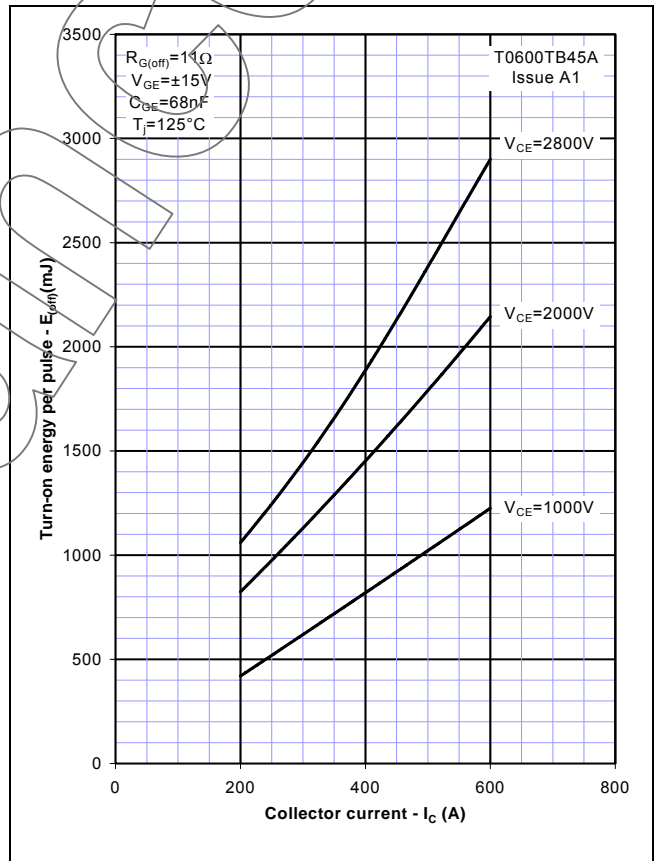


Figure 9 – Turn-on energy vs voltage

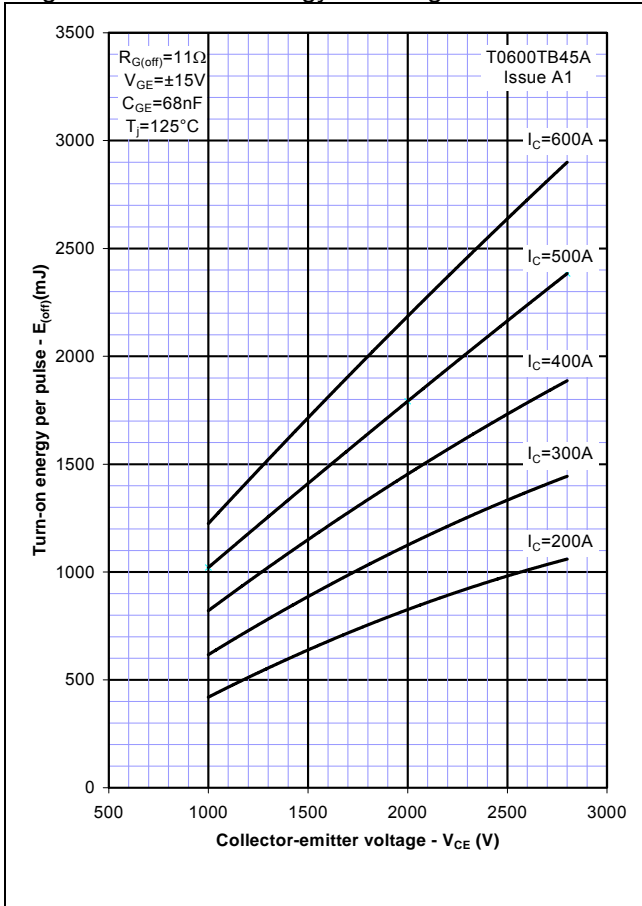


Figure 10 – Safe operating area

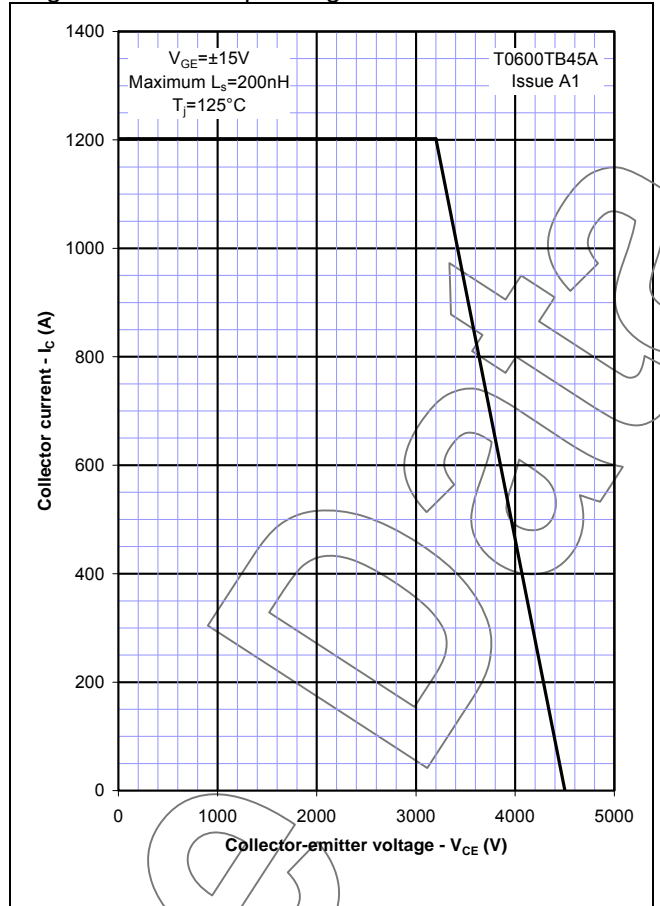


Figure 11 – Typical diode forward characteristic

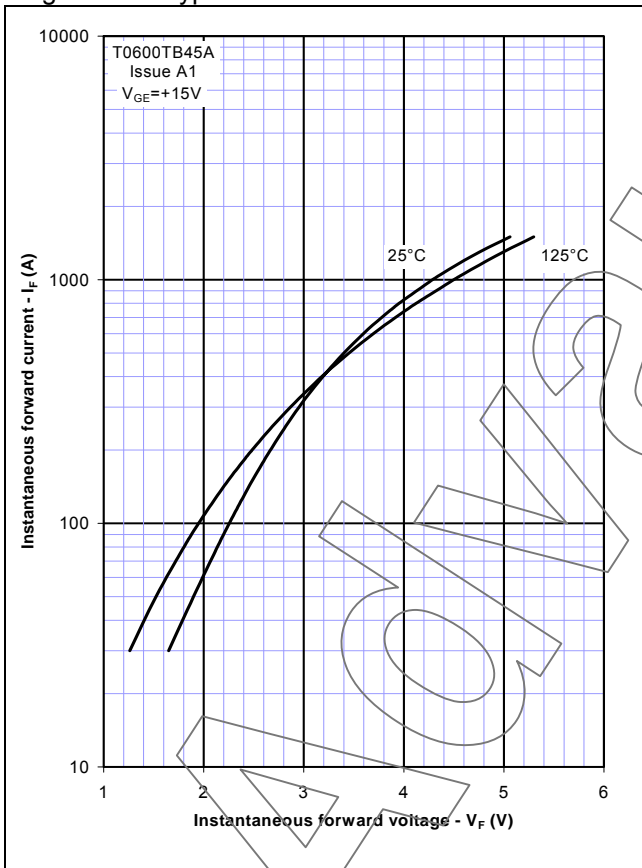


Figure 12 – Typical recovered charge

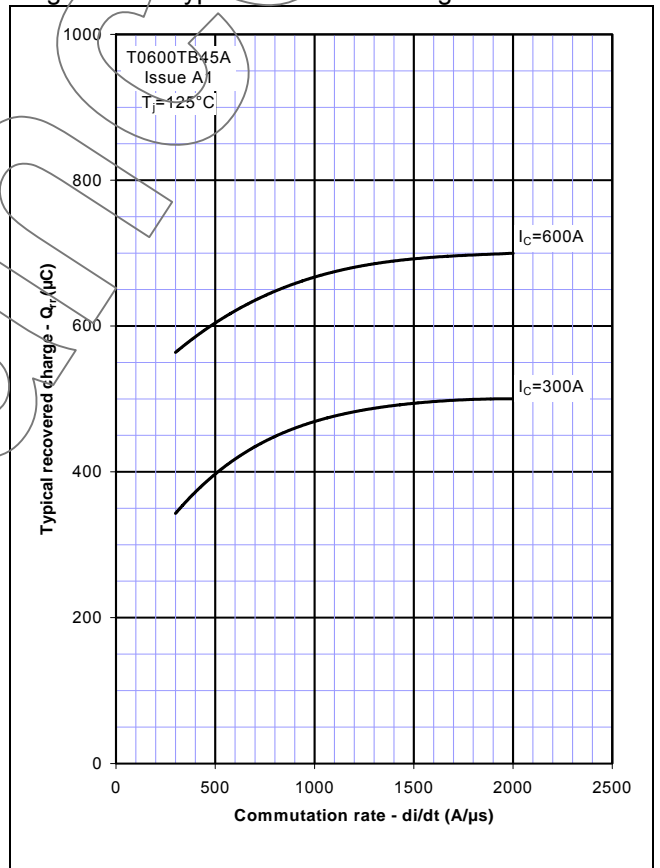


Figure 13 – Typical reverse recovery current

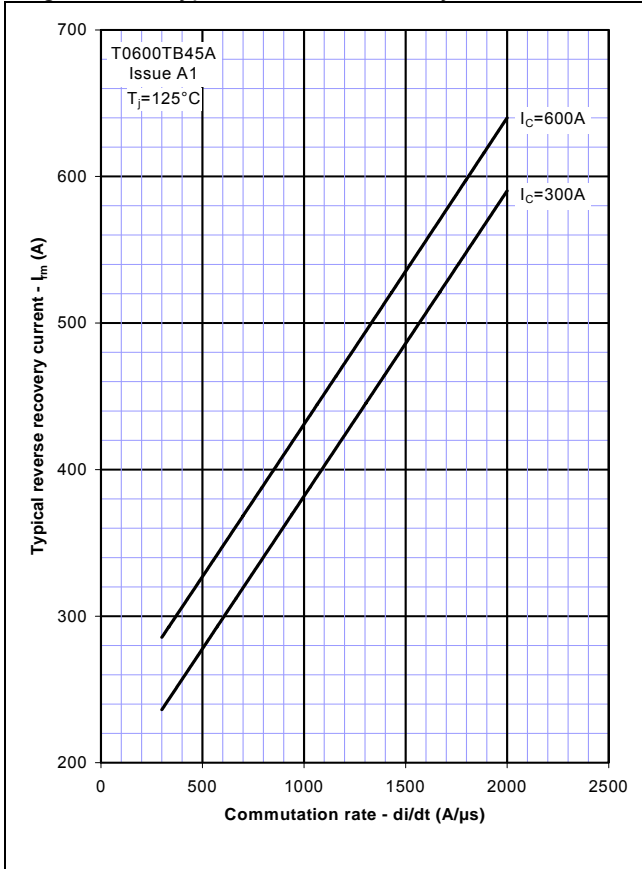


Figure 14 – Typical reverse recovery time

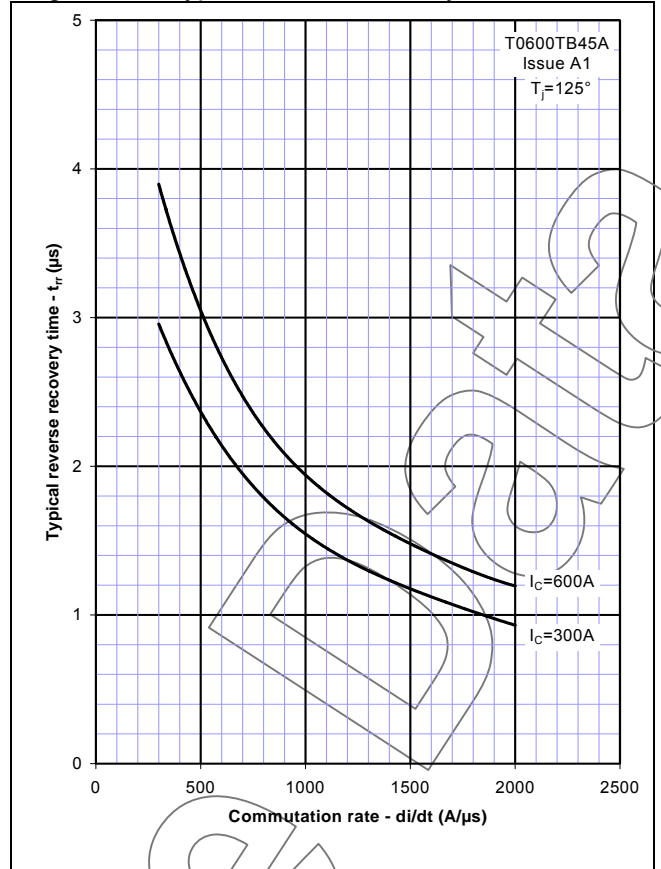


Figure 15 – Transient thermal impedance (IGBT)

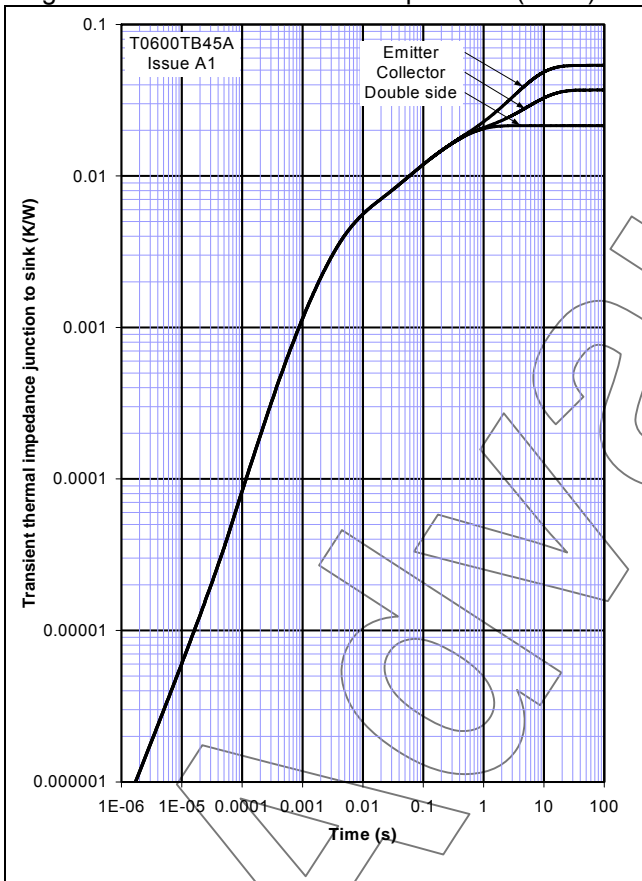
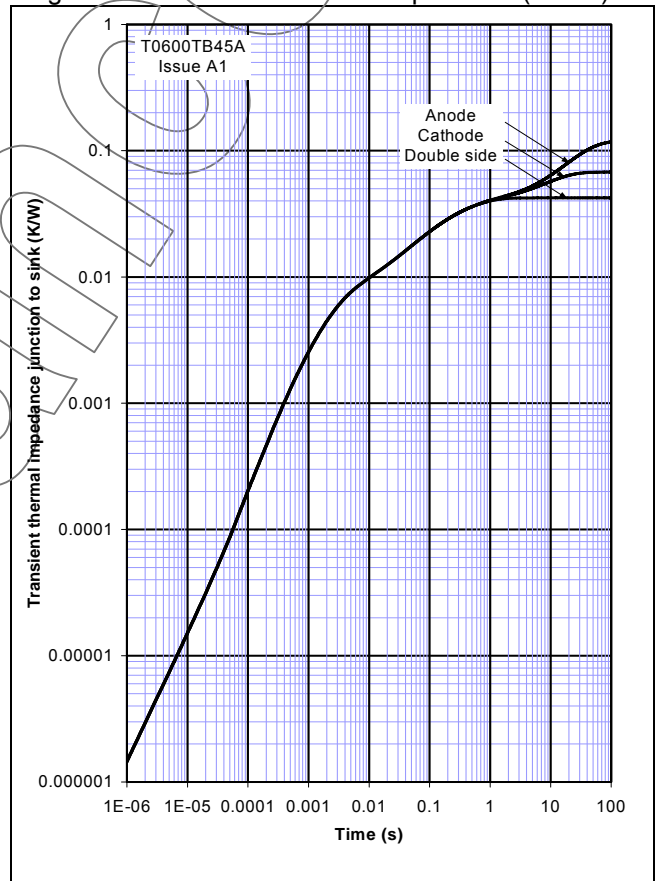
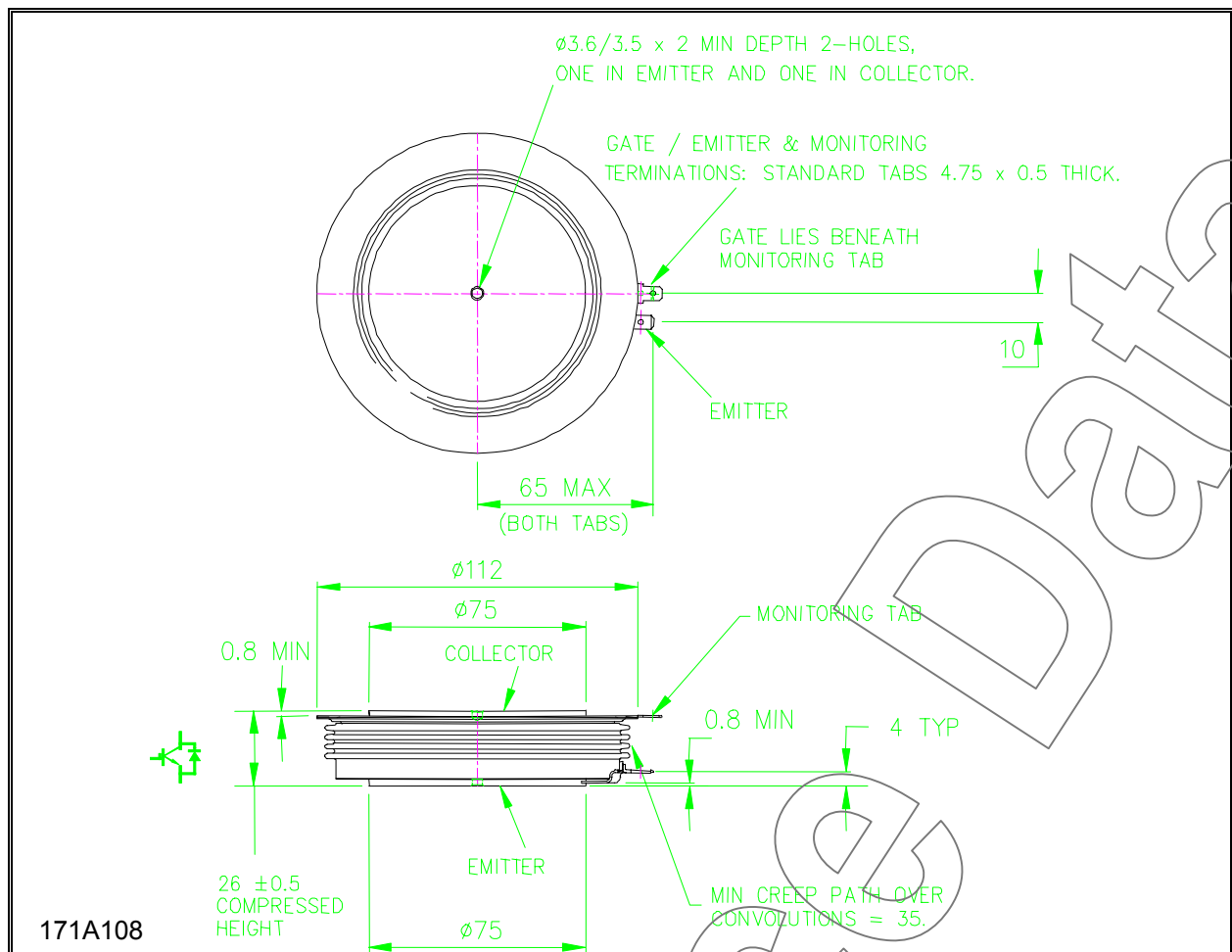


Figure 16 – Transient thermal impedance (Diode)



Outline Drawing & Ordering Information



ORDERING INFORMATION			
(Please quote 10 digit code as below)			
T0600	TB	45	A
Fixed type Code	Fixed Outline Code	Voltage Grade V _{CES} /100 45	Fixed format code

Typical order code: T0600TB45A (V_{CES} = 4500V)

IXYS Semiconductor GmbH
 Edisonstraße 15
 D-68623 Lampertheim
 Tel: +49 6206 503-0
 Fax: +49 6206 503-627
 E-mail: marcom@ixys.de

WESTCODE
 An IXYS Company

Westcode Semiconductors Ltd
 Langley Park Way, Langley Park,
 Chippenham, Wiltshire, SN15 1GE.
 Tel: +44 (0)1249 444524
 Fax: +44 (0)1249 659448
 E-mail: WSL.sales@westcode.com

IXYS Corporation
 1590 Buckeye Drive
 Milpitas CA 95035-7418
 Tel: +1 (408) 457 9000
 Fax: +1 (408) 496 0670
 E-mail: sales@ixys.net

www.westcode.com
www.ixys.net

IXYS Long Beach
 IXYS Long Beach, Inc
 2500 Mira Mar Ave, Long Beach
 CA 90815
 Tel: +1 (562) 296 6584
 Fax: +1 (562) 296 6585
 E-mail: service@ixyslongbeach.com

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